Application No.: NEW Docket No.: 0757-0316PUS1

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A microwave frequency converter comprising:

an RF amplifier capable of changing a gain to any value within a range from an amplified state to an attenuated state:

and a <u>control circuit</u> switch eircuit for applying a gain control voltage to the RF amplifier; wherein the <u>control circuit</u> switch eircuit controls the gain control voltage to be applied to the RF amplifier so as to cause the gain of the RF amplifier to be in the attenuated state during a period of time including a time during which a transmission section performs oscillation and times therebefore and thereafter, and to be in the amplified state during any period of time other than the period of time.

- 2. (Currently Amended) The microwave frequency converter according to claim 1, wherein the control circuit switch circuit continuously changes the gain control voltage to continuously change the gain of the RF amplifier from a predetermined gain value in the amplified state to a predetermined gain value in the attenuated state, or from a predetermined gain value in the attenuated state to a predetermined gain value in the amplified state.
- 3. (Currently Amended) The microwave frequency converter according to claim 1, wherein the control circuit switch-circuit instantaneously changes the gain control voltage to instantaneously change the gain of the RF amplifier from a predetermined gain value in the amplified state to a predetermined gain value in the attenuated state, or from a predetermined gain value in the attenuated state to a predetermined gain value in the amplified state.

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4. (Currently Amended) The microwave frequency converter according to claim 3, wherein the RF amplifier employs a FET device or a HEMT device which is operated by applying a negative voltage to a gate thereof and a positive voltage to a drain thereof, and the control circuit switch eireuit simultaneously switches ON/OFF a gate voltage and a drain voltage to be applied to the gate and the drain of the device to cause the gain of the RF amplifier to be in the attenuated state when the gate voltage and the drain voltage are switched ON, and to be in the amplified state when the gate voltage and the drain voltage are switched OFF.

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